Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT404 (D2PAK) surface mountable plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{i(max)}$ = 150 °C).

2. Features and benefits

- High bidirectional blocking voltage capability
- High junction operating temperature capability
- · High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Very high current surge capability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	_	800	V
V_{RRM}	repetitive peak reverse voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	210	Α
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 ms$	-	-	231	Α
T _j	junction temperature		-	-	150	°C





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 2;</u> <u>Fig. 3</u>		-	-	20	Α
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	4.5	32	mA
Dynamic chara	Dynamic characteristics						,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		300	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	K	cathode	mb	A - [] - K	
2	А	anode		G sym037	
3	G	gate			7
mb	Α	mounting base; connected to anode	1 3		
			D2PAK (SOT404)		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN20B-800T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Marking

Table 4. Marking codes

Type number	Marking code
TYN20B-800T	TYN20B-800T

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 1</u>	-	12.7	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	20	А
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5	-	210	A
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$	-	231	A
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	220.5	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 40 A; I_G = 200 mA; dI_G / dt = 200 mA/µs	-	50	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P _{GM}	peak gate power		-	20	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

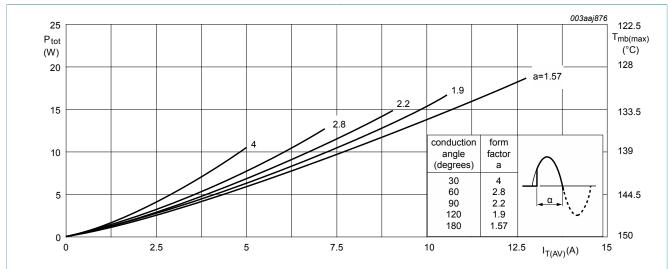


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

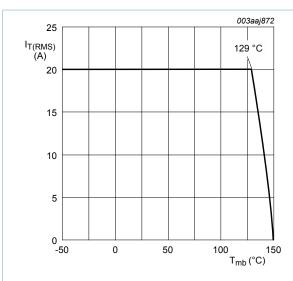
 $\mathbf{a} = \mathbf{form} \ \mathbf{factor} = \mathbf{I}_{T(RMS)} \, / \, \mathbf{I}_{T(AV)}$

TYN20B-800T

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Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

Fig. 3. RMS on-state current as a function of surge duration; maximum values

$$f = 50 \text{ Hz}; T_{mb} = 129 \text{ }^{\circ}\text{C}$$

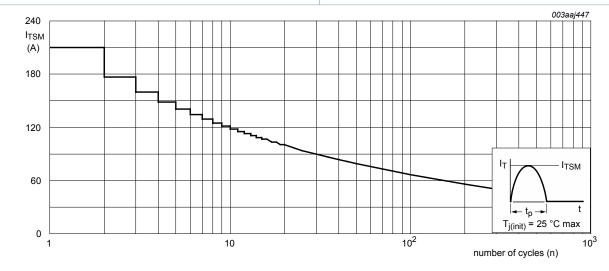


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

f = 50 Hz

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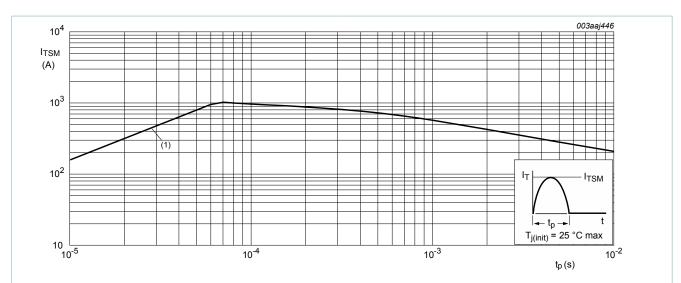


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values $t_p \leq 10 \; ms; \, (1) \; dI_T \, / \; dt \; limit$

9. Thermal characteristics

Table 6. Thermal characteristics

able of Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6		-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint, FR4 board		-	55	-	K/W

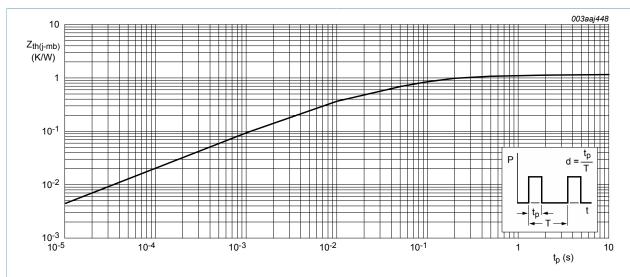


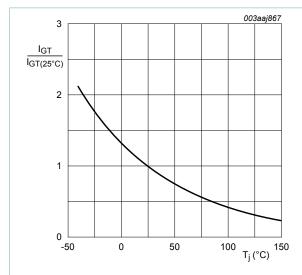
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	4.5	32	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	21	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	16	40	mA
V _T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1.3	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11	0.2	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 150 °C	-	0.2	1	mA
I _R	reverse current	V _R = 800 V; T _j = 150 °C	-	0.2	1	mA
Dynamic ch	naracteristics			'	'	,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	300	-	-	V/µs





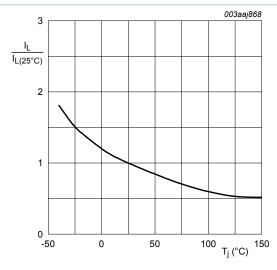


Fig. 8. Normalized latching current as a function of junction temperature

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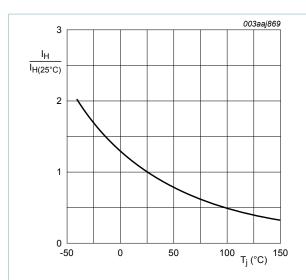
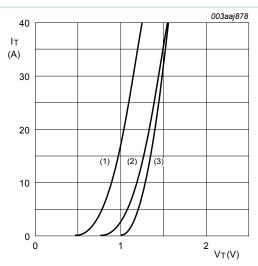


Fig. 9. Normalized holding current as a function of junction temperature



 V_{o} = 1.0485 V; R_{s} = 0.0133 Ω

(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

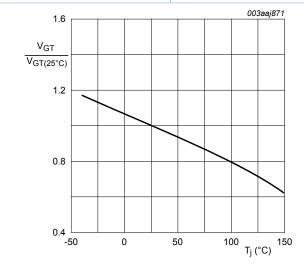
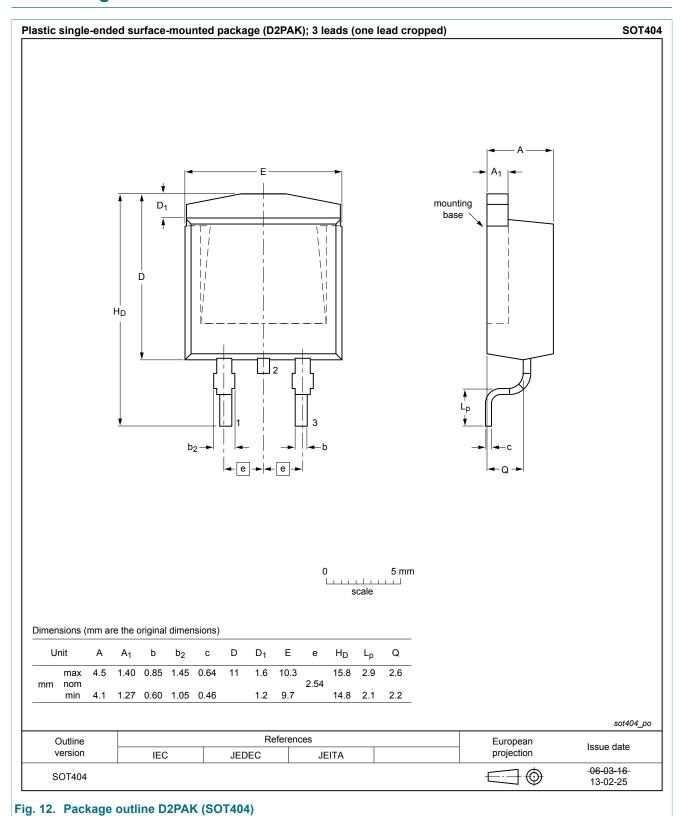


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

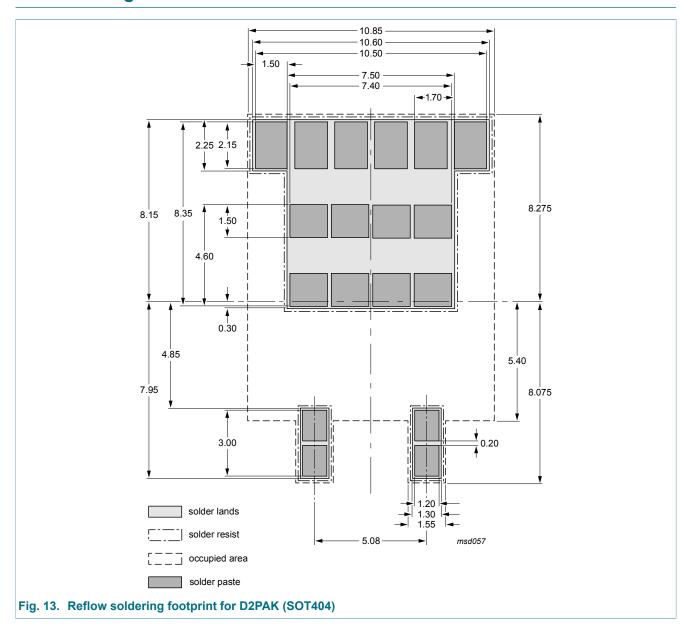
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11. Package outline



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12. Soldering



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13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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